

STX690A

High performance low voltage NPN transistor

Features

- Very low collector to emitter saturation voltage
- DC current gain, h_{FE} > 100
- 3 A continuous collector current
- 40 V breakdown voltage V_{(BR)CER}

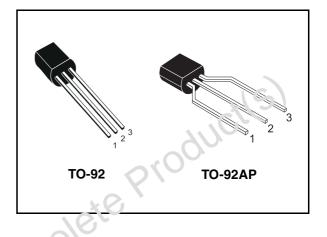
Applications

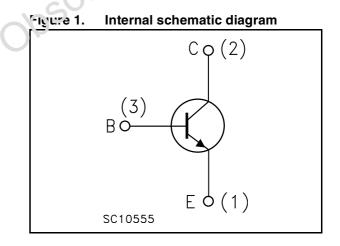
- Power management in portable equipment
- Voltage regulation in bias supply circuits
- Switching regulator in battery charger applications
- Heavy load driver

Description

21050lete

The device is manufactured in low voltage NFN planar technology by using a "Base Island" layout. The resulting transistor shows exceptional high gain performance coupled with very low saturation voltage.





Order code	Marking	Package	Packaging
STX690A	X690A	TO-92	Bulk
STX690A-AP	X690A	TO-92 AP	Ammopack

Electrical ratings 1

Table 2.	Absolute	maximum	ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	40	V
V _{CER}	Collector-emitter voltage ($R_{BE} = 47 \Omega$)	40	V
V _{CEO}	Collector-emitter voltage $(I_B = 0)$	30	V
V _{EBO}	Emitter-base voltage (I _C = 0)	5	v
۱ _C	Collector current	3 . [9	A
I _{CM}	Collector peak current (t _P < 5 ms)	6	А
P _{tot}	Total dissipation at T _{amb} = 25 °C	<u>Г</u> .э	W
T _{stg}	Storage temperature	-65 to 150	°C
Т _Ј	Max. operating junction temperature	150	°C
Table 3.	Thermal data		

Table 3. Thermal data

	Symbol Parameter			Value	Unit
	R _{thj-amb}	Thermal resistance junction-arb	max	139	°C/W
obsole	teP	roducils			

2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

Tai	JIE 4.							
	Symbol	Parameter	Test co	nditions	Min.	Тур.	Max.	Unit
	I _{CBO}	Collector cut-off current	V _{CB} = 30 V				10	μA
	-CBO	(I _E = 0)	V _{CB} = 30 V;	T _C = 100 °C			100	μA
	I _{EBO}	Emitter cut-off current $(I_{\rm C} = 0)$	V _{EB} = 4 V				10	μA
V ₍	BR)CEO ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = 10 mA		30	JU		v
v ₍	BR)CER ⁽¹⁾	Collector-emitter breakdown voltage ($R_{BE} = 47 \Omega$)	I _C = 10 mA		40			V
	(BR)CBO	Collector-base breakdown voltage (I _E = 0)	l _C = 100 μA	1610	40			V
\	(BR)EBO	Emitter-base breakdown voltage (I _C = 0)	. <u>-</u> = 100 μA		5			V
		16	I _C = 0.5 A	I _B = 5 mA		0.08	0.15	V
		d	I _C = 1.2 A	I _B = 20 mA		0.1	0.22	V
V	CE(sat) ⁽¹⁾	Colluctor emitter	I _C = 2 A	I _B = 20 mA		0.175	0.35	V
		saturation voltage	I _C = 3 A	I _B = 100 mA		0.2	0.4	V
	0		I _C = 3 A	I _B = 100 mA				
	2		T _C = 100 °C			0.3		V
	BE(sat) ⁽¹⁾	Base-emitter saturation voltage	I _C = 1 A	I _B = 10 mA		0.8	1	V
V	BE(on) ⁽¹⁾	Base-emitter on voltage	I _C = 1 A	$V_{CE} = 2 V$		0.8	1	V
			I _C = 10 mA	V _{CE} = 2 V	100	200	400	
			l _C = 500 mA	V _{CE} = 2 V	100	200	400	
	h _{FE} ⁽¹⁾	DC current gain	I _C = 1 A	V _{CE} = 2 V	100			
	· -	-	I _C = 2 A	$V_{CE} = 1 V$	100	160		
			I _C = 3 A	$V_{CE} = 1 V$	90	130		

Table 4. Electrical characteristics

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DC current train

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
f _t	Transition frequency	$I_{C} = 50 \text{ mA}$ $V_{CE} = 5 \text{ V}$ f = 50 MHz		100		MHz
	Resistive load					
t _d	Delay time	$I_{\rm C} = 3 \text{ A}$ $V_{\rm CC} = 20 \text{ V}$		50		ns
t _r	Rise time	I _{B1} = -I _{B2} = 60 mA		120		ns
t _s	Storage time	see Figure 8		465		ns
t _f	Fall time			80		ns

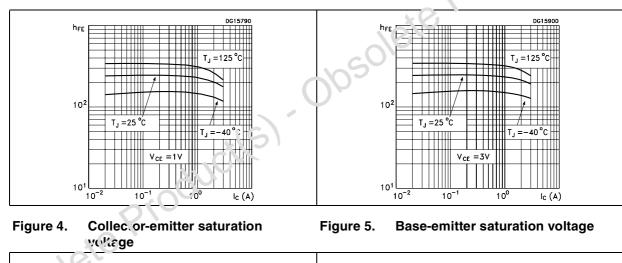
Figure 3.

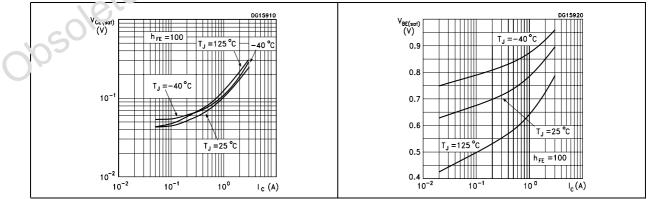
 Table 4.
 Electrical characteristics (continued)

1. Pulse duration = 300 μ s, duty cycle \leq 1.5%

2.1 Electrical characteristics (curves)

Figure 2. DC current gain



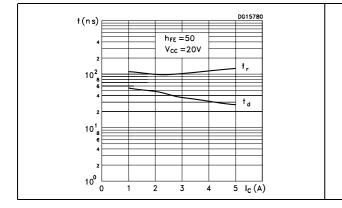


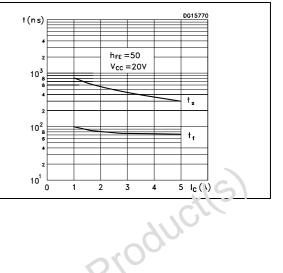


STX690A

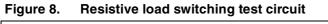
Figure 6. Switching time resistive load

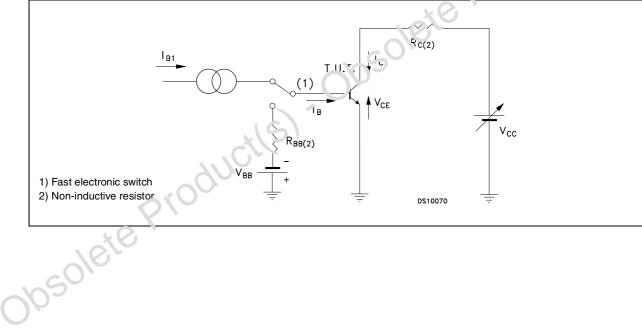
Figure 7. Switching time resistive load





2.2 Test circuit







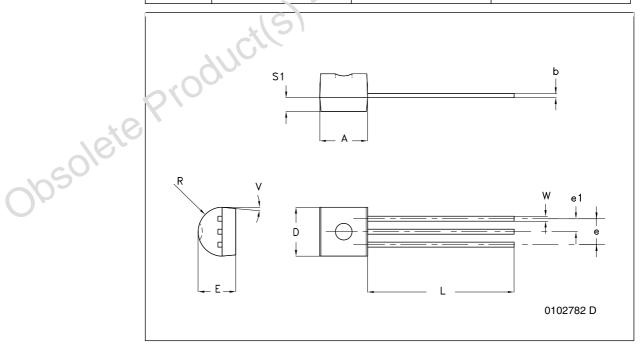
3 Package mechanical data

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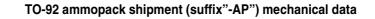
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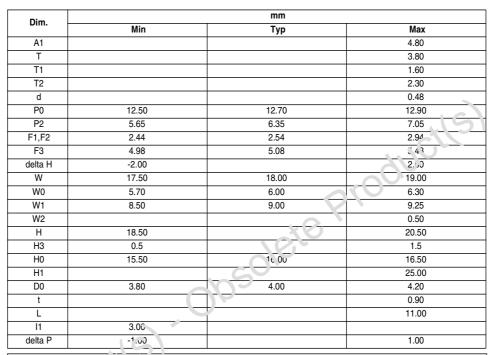
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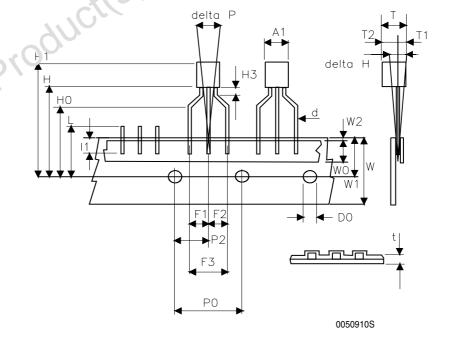
	TO-92 bulk shipment mechanical data				
		mm.			
DIM.	MIN.	ТҮР	MAX.		
А	4.32		4.95		
b	0.36		0.51		
D	4.45		4.95		
E	3.30		354		
е	2.41		2.67		
e1	1.14	0	1.40		
L	12.70	×C	15.49		
R	2.16	16,	2.41		
S1	0.92	GO!	1.52		
W	0.41	10-	0.56		
V		5°			



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Obsolete

4 Revision history

Table 5.Document revision history

Date	Revision	Changes
09-Feb-2009	1	Initial release.

obsolete Product(s) - Obsolete Product(s)

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